



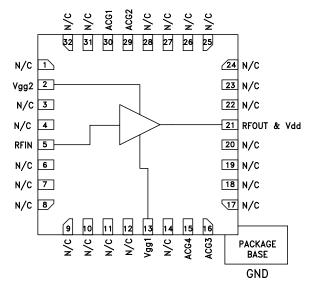
v07.0418

Typical Applications

The HMC465LP5(E) wideband driver is ideal for:

- OC192 LN/MZ Modulator Driver
- Microwave Radio & VSAT
- Test Instrumentation
- Military EW, ECM & C3I

Functional Diagram



GaAs PHEMT MMIC MODULATOR DRIVER AMPLIFIER, DC - 20 GHz

Features

Gain: 15 dB Output Voltage to 10Vpk-pk +24 dBm Saturated Output Power Supply Voltage: +8V @160 mA 50 Ohm Matched Input/Output 32 Lead 5x5 mm QFN Package: 25 mm²

General Description

The HMC465LP5(E) is a GaAs MMIC PHEMT Distributed Driver Amplifier packaged in leadless 5x5 mm surface mount package which operate between DC and 20 GHz. The amplifier provides 15 dB of gain, 3 dB noise figure and +25 dBm of saturated output power while requiring only 160 mA from a +8V supply. Gain flatness is excellent at ± 0.5 dB as well as ± 4 deg deviation from linear phase from DC - 10 GHz making the HMC465LP5(E) ideal for OC192 fiber optic LN/MZ modulator driver amplifiers as well as test equipment applications. The HMC465LP5(E) amplifiers I/Os are internally matched to 50 Ohms.

Electrical Specifications, $T_A = +25^{\circ}$ C, Vdd= 8V, Vgg2= 1.5V, Idd= 160 mA*

| Parameter | Min. | Тур. | Max. | Min. | Тур. | Max. | Min. | Тур. | Max. | Units |
|---|--------|-------|------------|------|-------------|-------|------|-------|-------|--------|
| Frequency Range | DC - 6 | | 6.0 - 12.0 | | 12.0 - 20.0 | | | GHz | | |
| Gain | 13 | 16 | | 12 | 15 | | 9.5 | 12.5 | | dB |
| Gain Flatness | | ±0.75 | | | ±0.25 | | | ±1.5 | | dB |
| Gain Variation Over Temperature | | 0.015 | 0.02 | | 0.020 | 0.025 | | 0.035 | 0.045 | dB/ °C |
| Noise Figure | | 3.0 | | | 3.0 | | | 4.0 | | dB |
| Input Return Loss | | 20 | | | 15 | | | 8 | | dB |
| Output Return Loss | | 22 | | | 17 | | | 12 | | dB |
| Output Power for 1 dB Compression (P1dB) | 21 | 24 | | 20 | 23 | | 16 | 20 | | dBm |
| Saturated Output Power (Psat) | | 25.5 | | | 25 | | | 23 | | dBm |
| Output Third Order Intercept (IP3) | | 32 | | | 28 | | | 24 | | dBm |
| Saturated Output Voltage | | 10 | | | 10 | | | 8 | | Vpk-pk |
| Group Delay Variation | | ±15 | | | ±15 | | | | | pSec |
| Supply Current (Idd) (Vdd= 8V, Vgg1= -0.6V Typ.) | | 160 | | | 160 | | | 160 | | mA |

* Adjust Vgg1 between -2 to 0V to achieve Idd= 160 mA typical.

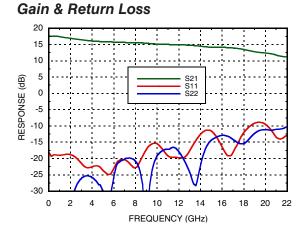
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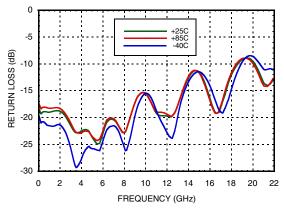




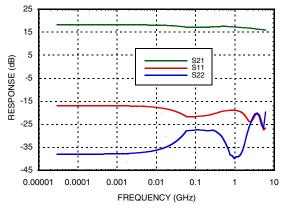
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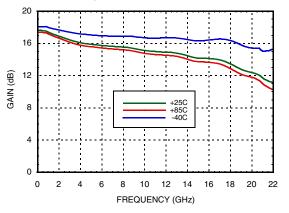
Input Return Loss vs. Temperature



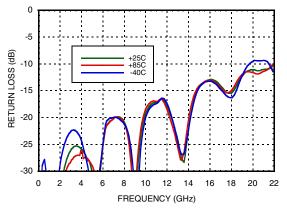
Low Frequency Gain & Return Loss



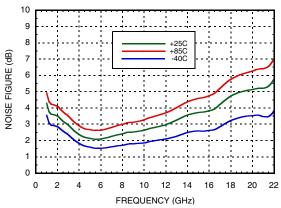
Gain vs. Temperature



Output Return Loss vs. Temperature



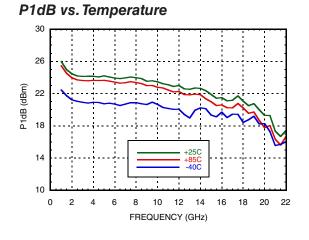
Noise Figure vs. Temperature



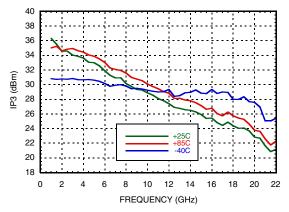




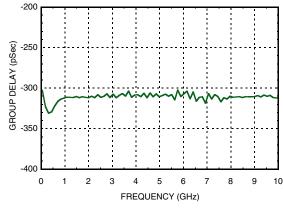
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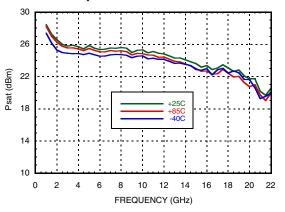
Output IP3 vs. Temperature



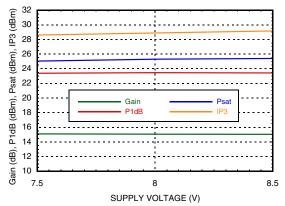
Group Delay



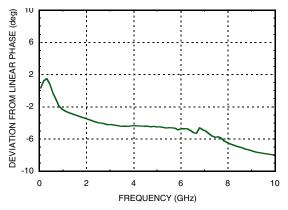
Psat vs. Temperature



Gain, Power & Output IP3 vs. Supply Voltage @ 10 GHz, Idd = 160mA



Deviation from Linear Phase







GAAS PHEMT MMIC MODULATOR DRIVER AMPLIFIER, DC - 20 GHz

Absolute Maximum Ratings

| Drain Bias Voltage (Vdd) | +9 Vdc |
|---|------------------------|
| Gate Bias Voltage (Vgg1) | -2 to 0 Vdc |
| Gate Bias Current (Igg1) | +3.2mA |
| Gate Bias Voltage (Vgg2) | (Vdd -8) Vdc to +3 Vdc |
| Gate Bias Current (Igg2) | +3.2mA |
| RF Input Power (RFIN)(Vdd = +8 Vdc) | +23 dBm |
| Channel Temperature | 150 °C |
| Continuous Pdiss (T = 85 °C) (derate 24 mW/°C above 85 °C) | 1.56 W |
| Thermal Resistance (channel to ground paddle) | 41.5 °C/W |
| Storage Temperature | -65 to +150 °C |
| Operating Temperature | -40 to +85 °C |

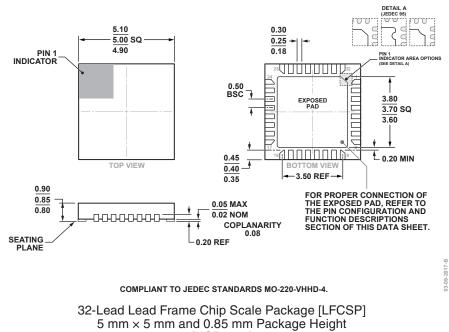
Typical Supply Current vs. Vdd

| Vdd (V) | ldd (mA) |
|---------|----------|
| +7.5 | 161 |
| +8.0 | 160 |
| +8.5 | 159 |



ELECTROSTATIC SENSITIVE DEVICE OBSERVE HANDLING PRECAUTIONS

Outline Drawing



(HCP-32-1)

Dimensions shown in millimeters.

Package Information

| Part Number | Package Body Material | Lead Finish | MSL Rating | Package Marking ^[3] | |
|-------------|--|---------------|---------------------|--------------------------------|--|
| HMC465LP5 | Low Stress Injection Molded Plastic | Sn/Pb Solder | MSL1 ^[1] | H465 XXXX | |
| HMC465LP5E | RoHS-compliant Low Stress Injection Molded Plastic | 100% matte Sn | MSL1 ^[2] | <u>H465</u> XXXX | |

[1] Max peak reflow temperature of 235 °C

[2] Max peak reflow temperature of 260 °C

[3] 4-Digit lot number XXXX

For price, delivery, and to place orders: Analog Devices, Inc., One Technology Way, P.O. Box 9106, Norwood, MA 02062-9106 Phone: 781-329-4700 • Order online at www.analog.com Application Support: Phone: 1-800-ANALOG-D



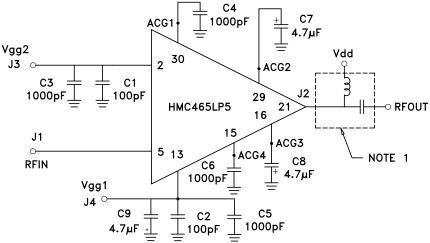


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Pin Descriptions

| Pin Number | Function | Description | Interface Schematic | | |
|--|----------------|--|------------------------------|--|--|
| 1, 3, 4, 6 - 12, 14, 17, 18, 19, 20, 22 - 28, 31, 32 | N/C | The pins are not connected internally; however, all data shown herein was measured with these pins connected to RF/DC ground externally. | | | |
| 2 | Vgg2 | Gate Control 2 for amplifier. +1.5V should be applied to Vgg2 for nominal operation. | Vgg2 | | |
| 5 | RFIN | This pad is DC coupled and matched to 50 Ohms. | | | |
| 13 | Vgg1 | Gate Control 1 for amplifier. | Vgg10 | | |
| 15 | ACG4 | | RFIN C ACG4 ACG3 | | |
| 16 | ACG3 | Low frequency termination. Attach bypass capacitor per application circuit herein. | | | |
| 21 | RFOUT & Vdd | RF output for amplifier. Connect the DC bias (Vdd) network to provide drain current (Idd). See application circuit herein. | ACG1 0 RFOUT & ACG2 0 Vdd | | |
| 29 | ACG2 | Low frequency termination. Attach bypass capacitor per | | | |
| 30 | ACG1 | application circuit herein. | | | |
| Ground Paddle | GND | Ground paddle must be connected to RF/DC ground. | | | |

Application Circuit



NOTE 1: Drain Bias (Vdd) must be applied through a broadband bias tee or external bias network.

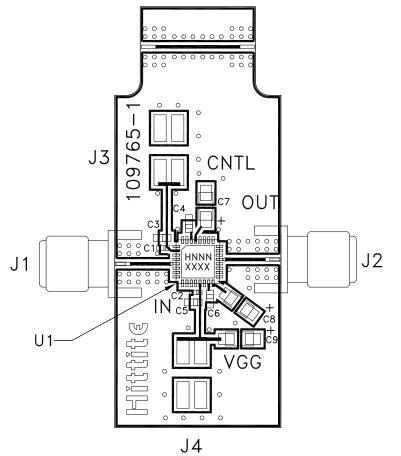






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Evaluation PCB



List of Materials for Evaluation PCB 108347 [1]

| Item | Description |
|---------|------------------------------|
| J1 - J2 | SRI K Connector |
| J3 - J4 | 2mm Molex Header |
| C1, C2 | 100 pF Capacitor, 0402 Pkg. |
| C3 - C6 | 1000 pF Capacitor, 0603 Pkg. |
| C7 - C9 | 4.7 µF Capacitor, Tantalum |
| U1 | HMC465LP5 / HMC465LP5E |
| PCB [2] | 109765 Evaluation PCB |

Reference this number when ordering complete evaluation PCB
Circuit Board Material: Rogers 4350

The circuit board used in the final application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and package bottom should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Analog Devices, upon request.





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Device Operation

These devices are susceptible to damage from Electrostatic Discharge. Proper precautions should be observed during handling, assembly and test.

The input to this device should be AC-coupled. To provide the typical 8Vp-p output voltage swing, a 1.2Vp-p AC-coupled input voltage swing is required.

Device Power Up Instructions

- 1. Ground the device
- 2. Set Vgg to -2V (no drain current)
- 3. Set Vctl to +1V (no drain current)
- 4. Set Vdd to +5V (no drain current)
- 5. Adjust Vgg for Idd = 140mA
- Vgg may be varied between -1V and 0V to provide the desired eye crossing point percentage (i.e. 50% crosspoint) and a limited cross point control capability.
- Vdd may be increased to +8V if required to achieve greater output voltage swing.
- Vctl may be adjusted between +2V and +0V to vary the output voltage swing.

Device Power Down Instructions

1. Reverse the sequence identified above in steps 1 through 4.